





Small Signal Diode



Features

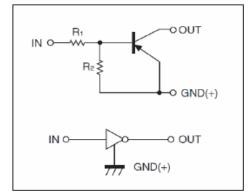
- ♦Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistor (see equivalent circuit).
- ♦TheThe bias resistors consist of thin -film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completel yeliminating parasitic effects.
- ♦Only the on/off conditions need to be set for operation,marking device design easy.

Ordering Information

Package	Part No.	Packing	Marking
SOT-723	DTA114 EM	8K / 7" Reel	14
SOT-523	DTA114 EE	3K / 7" Reel	14
SOT-323	DTA114 EUA	3K / 7" Reel	14
SOT-23	DTA114 ECA	3K / 7" Reel	14
TO-92S	DTA114 ESA	3K / 7" Reel	

DTA114 EM/EE/EUA/ECA/ESA PNP Digital Transistor

Equivalent Circuit





SOT-723/SOT-523 SOT-323/SOT-23

1.IN 2.GND

3.OUT

TO-92S

1.GND

2.OUT

3.IN

Maximum Ratings and Electrical Characteristics

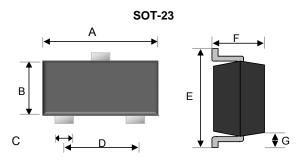
Rating at 25°C ambient temperature unless otherwise specified.

Towns November	Symbol	Value				11-26-
Type Number		EM	EE	EUA ECA	ESA	Units
Power Dissipation	PD	100	150	200	300	mW
Supply Voltage	V_{CC}	-50			V	
Input Voltage	V_{IN}	-40 ∼10				V
Output Current	Io	-50				mA
PeakCollectoCurrent	I _{C(MAX)}	-100				IIIA
Junction and Storage Temperature Range	TJ, T _{STG}	-55 to + 150				°C

Notes:1. Valid provided that electrodes are kept at ambient temperature

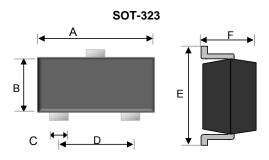
Parameter	Symbol	Min	Min Typ		Condtion	Unit	
	$V_{I(on)}$			-3	V _{CC} =-5V,I _O =-100μA		
Input Voltage	V _{I(off)}	-0.5			V _O =-0.3V,I _O =-10mA	V	
Output Voltage	$V_{O(on)}$			-0.3	I _O /I _I =-10mA/-5mA	V	
Input Current	l _l			-0.88	V _I =-5V	mA	
Output Current	I _{O (off)}			-0.5	V _{CC} =-50V,V _I =0	μΑ	
DC Current Gain	G	30			V_0 =-5 V , I_0 =-5 mA		
Input Resistance	R ₁	7	10	13		ΚΩ	
Resistance Ratio	R_2/R_1	0.8	1	1.2			
Transition Frequency	f _T		250		$V_0 = -10V, I_0 = -5mA, f = 100MHz$	MHz	



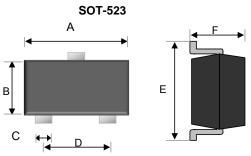


Dimensions	Unit	(mm)	Unit (inch)		
Dilliensions	Min	Max	Min	Max	
Α	2.80	3.00	0.11	0.12	
В	1.20	1.40	0.05	0.06	
С	0.30	0.50	0.01	0.02	
D	1.80	2.00	0.07	0.08	
Е	2.25	2.55	0.09	0.10	
F	0.90	1.20	0.04	0.04	
G	0.550 REF		0.022 REF		

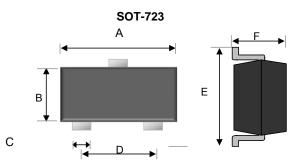
DTA114 EM/EE/EUA/ECA/ESA PNP Digital Transistor



Dimensions	Unit ((mm)	Unit (inch)		
Dillielisions	Min	Max	Min	Max	
Α	1.90	2.10	0.07	0.08	
В	1.15	1.35	0.05	0.05	
С	0.25	0.35	0.01	0.01	
D	1.20	1.40	0.05	0.06	
E	2.00	2.20	0.08	0.09	
F	0.80	1.00	0.03	0.04	



Dimensions	Unit	(mm)	Unit (inch)		
Dilliensions	Min	Max	Min	Max	
Α	1.50	1.70	0.06	0.07	
В	0.70	0.80	0.03	0.03	
С	0.25	0.35	0.01	0.01	
D	0.90	1.10	0.04	0.04	
E	1.50	1.70	0.06	0.07	
F	0.70	0.90	0.03	0.04	



Dimensions	Unit	(mm)	Unit (inch)		
Difficusions	Min	Max	Min	Max	
Α	1.15	1.25	0.05	0.05	
В	0.75	0.85	0.03	0.03	
С	0.17	0.27	0.01	0.01	
D	0.8 TYP		0.31	ITYP	
Е	1.15	1.25	0.05	0.05	
F		0.50		0.02	

